UTC UNISONIC TECHNOLOGIES CO., LTD

2SA1201

PNP SILICON TRANSISTOR

SILICON PNP EPITAXIAL TRANSISTOR

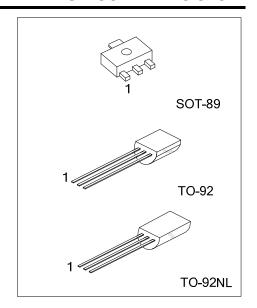
DESCRIPTION

The UTC 2SA1201 is designed for power amplifier and voltage amplifier applications.

FEATURES

*High voltage: V_{CEO}= -120V

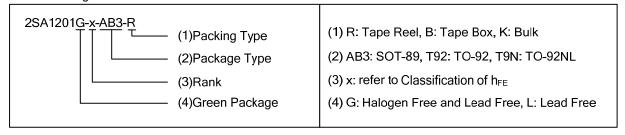
*High transition frequency: f_T=120MHz(typ.) *P_c=1 to 2 W(mounted on ceramic substrate)



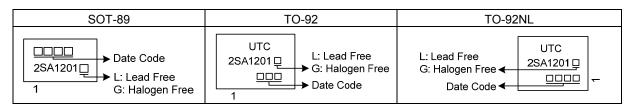
ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
2SA1201L-x-AB3-R	2SA1201G-x-AB3-R	SOT-89	В	С	Е	Tape Reel	
2SA1201L-x-T92-B	2SA1201G-x-T92-B	TO-92	Е	С	В	Tape Box	
2SA1201L-x-T92-K	2SA1201G-x-T92-K	TO-92	Е	С	В	Bulk	
2SA1201L-x-T9N-B	2SA1201G-x-T9N-B	TO-92NL	Е	С	В	Tape Box	
2SA1201L-x-T9N-K	2SA1201G-x-T9N-K	TO-92NL	E	С	В	Bulk	

Note: Pin Assignment: B: Base C: Collector E: Emitter



MARKING



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■ **ABSOLUTE MAXIMUM RATINGS** (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	-120	V
Collector-Emitter Voltage		$V_{\sf CEO}$	-120	V
Emitter-Base Voltage		V_{EBO}	-5	V
Collector Current		Ic	-800	mA
Base Current		Ι _Β	-160	mA
Collector Power Dissipation	SOT-89		500	mW
		Pc	1000 (Note 2)	mW
	TO-92/TO-92NL		600	mW
Junction Temperature		T_J	150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

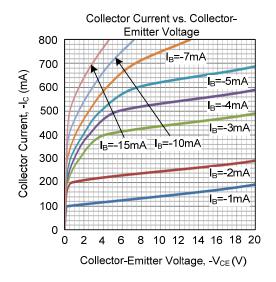
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	I _C = -10mA, I _B =0	-120			V
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	I _E = -1mA, I _C =0	-5			V
Collector Cut-Off Current	I _{CBO}	V _{CB} = -120V, I _E =0			-0.1	μΑ
Emitter Cut-Off Current	I _{EBO}	V _{EB} = -5V, I _C =0			-0.1	μΑ
DC Current Gain	h _{FE}	V _{CE} = -5V, I _C = -100mA	80		240	
Collector to Emitter Saturation Voltage	$V_{CE(SAT)}$	I _C = -500mA, I _B = -50mA			-1.0	V
Base to Emitter Voltage	V_{BE}	V _{CE} = -5V, I _C = -100mA			-1.0	V
Transition Frequency	f _T	V _{CE} = -5V, I _C = -100mA		120		MHz
Collector Output Capacitance	Сов	V _{CB} = -10V, I _E =0, f=1MHz			30	pF

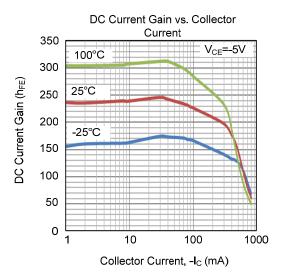
■ CLASSIFICATION OF h_{FE}

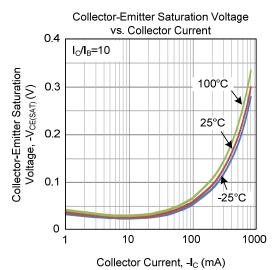
RANK	0	Υ
RANGE	80 - 160	120 - 240

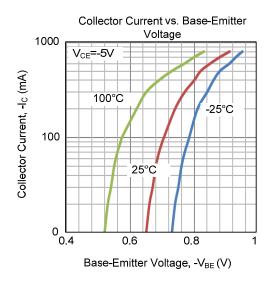
^{2.} Mounted on cermic substrate(250mm² × 0.8t)

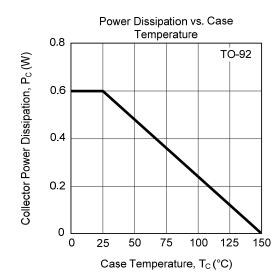
■ TYPICAL CHARACTERISTICS

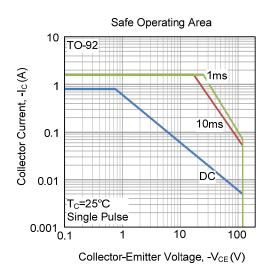












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